

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 20 A, 650 V, D1, TO-247-3L

FFSH2065ADN-F155

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching charactristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

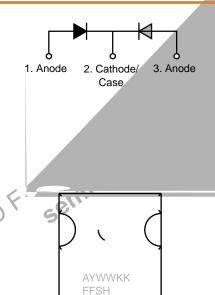
Features

- Max Junction Temperature 175°C
- Avalanche Rated 64 mJ

- No Reverse Recovery/No Forward Recovery
 This Device is Pb—Free, Halogen Free/BFR Free and RoHS Compliant

 Applications
 General Purpose
 SMPS, Solar Inverter, UPS
 Power Switching Circuits





2065ADN

= Assembly Plant Code = Date Code (Year & Week) = Lot Traceability Code FFSH2065ADN = Specific Device Code

THIS DEVICE IS NO

DISCONTINUED

